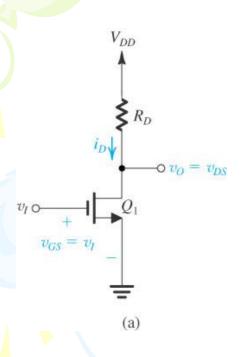
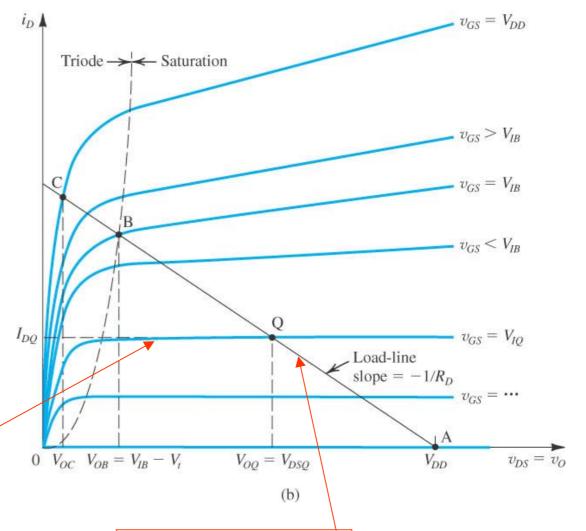
# Lecture 08 MOSFET's Circuit



- 1. Large-signal operation
- 2. FET circuits at DC
- 3. FET biasing schemes

#### Large-signal operation

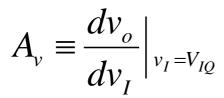


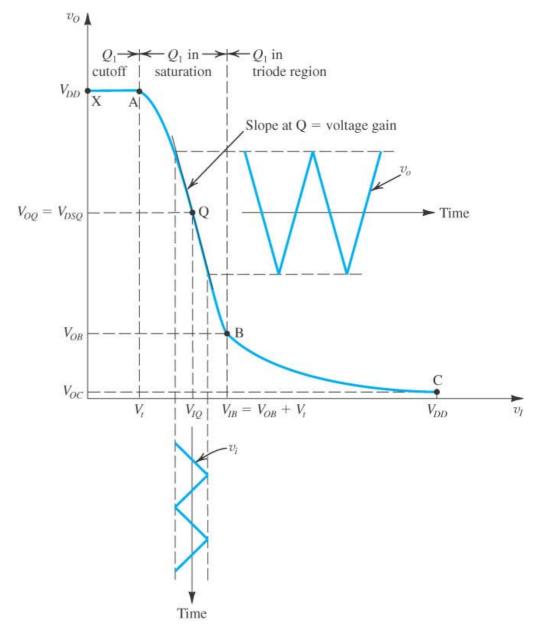


$$I_D = \frac{\mu C_o w}{2L} (v_{GS} - V_t)^2$$

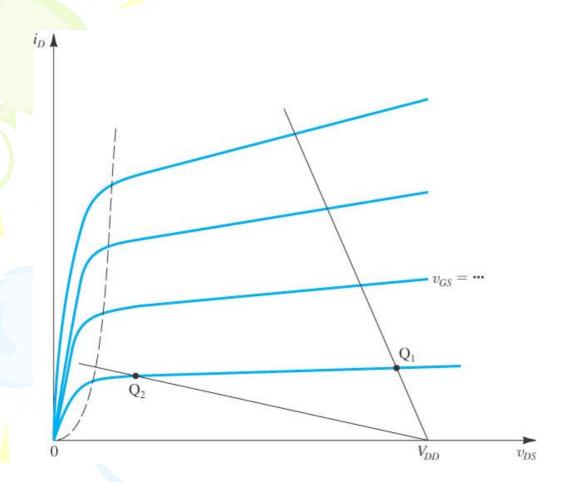
$$I_D = \frac{k_n'w}{2L}(v_{GS} - V_t)^2$$
 Load line:  $V_{DD} = i_D R_D + v_{DS}$ 

$$V_{DD} = i_D R_D + v_{DS}$$

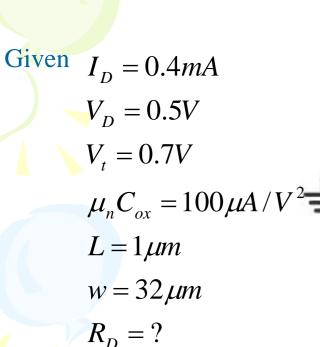




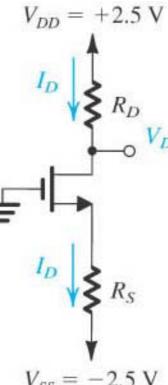
(c)



#### DC analysis



 $R_{\rm s}=?$ 



$$I_D = \frac{\mu C_o w}{2L} (v_{GS} - V_t)^2$$

$$\Rightarrow v_{GS} = 1.2V$$

$$\Rightarrow V_{GS} = 1.2V$$

$$V_S = I_D R_S + V_{SS}$$

$$\Rightarrow V_S = I_D R_S - 2.5V$$

$$R_s = \frac{-1.2 + 2.5}{0.4m} = 3.25k$$

$$V_{DD} = I_D R_D + V_D$$

$$\Rightarrow 2.5V = I_D R_D + V_D$$

$$2.5 - 0.5$$

$$R_D = \frac{2.5 - 0.5}{0.4m} = 5k$$

#### Given

$$I_D = 80 \mu A$$

$$V_{t} = 0.6V$$

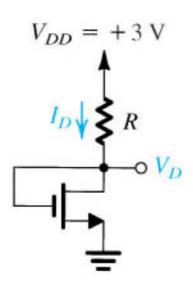
$$\mu_n C_{ox} = 200 \mu A/V^2$$

$$L = 0.8 \mu m$$

$$w = 4 \mu m$$

$$V_D = ?$$

$$R = ?$$



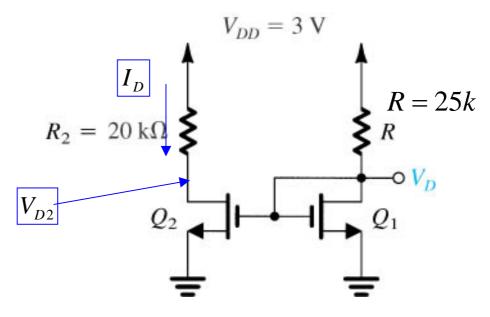
$$I_D = \frac{\mu C_o w}{2L} (V_D - V_t)^2$$

$$\Rightarrow V_D = 1V$$

$$V_{DD} = 3V = I_D R + V_D$$

$$\Rightarrow R = \frac{3-1}{0.08m} = 25k$$

#### Exercise 4.12



$$I_{D} = \frac{\mu C_{o} w}{2L} (V_{GS2} - V_{t})^{2} = \frac{\mu C_{o} w}{2L} (V_{D} - V_{t})^{2}$$

$$\therefore V_{D} = 1V \therefore I_{D} = 80 \,\mu\text{A}$$

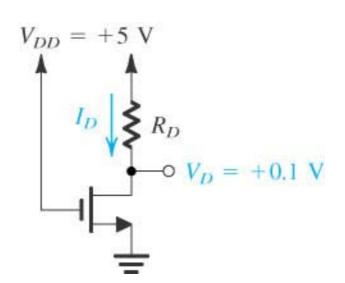
$$V_{DD} = 3V = I_{D} R_{2} + V_{D2}$$

$$\Rightarrow V_{D2} = 3 - 80 \,\mu \times 20 k = 1.4V$$

$$V_t = 1V$$

$$K'_n(W/L) = 1mA/V^2$$

$$find R_D = ?$$

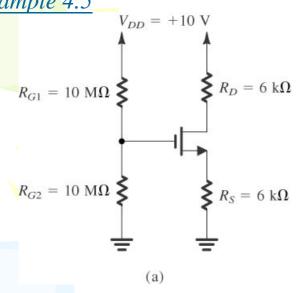


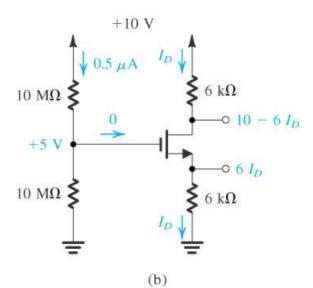
$$v_{DS} = V_D = 0.1V \le V_{DD} - V_t = 5 - 1 = 4$$
  
 $v_{DS} \le v_{GS} - V_t \rightarrow ohmic \quad region$ 

$$I_{D} = \frac{\mu_{n} C_{o} w}{2L} [2(v_{GS} - V_{t}) v_{DS} - v_{DS}^{2}]$$

$$\to I_{D} = 0.395 mA$$

$$R_D = \frac{5 - 0.1}{0.395m} = 12.4k$$





let

$$V_{t} = 1V$$

$$K_n'(W/L) = 1mA/V^2$$

Assume FET in saturation mode since  $V_G>0$ 

$$V_G = \frac{10M}{10M + 10M} 10V = 5V$$

$$I_{D} = \frac{1}{2} k_{n}^{'} \frac{W}{L} (V_{GS} - V_{t})^{2}$$

$$\Rightarrow I_D = \frac{1}{2} \times 1 \times [(5 - I_D \times 6k) - 1]^2$$

$$\Rightarrow 18I_D^2 - 25I_D + 8 = 0$$

$$I_D = 0.89mA, I_D = 0.5mA$$

if 
$$I_D = 0.89 mA$$

$$V_S = 6k \times 0.89m = 5.34V$$

$$\rightarrow V_{GS} < 0$$
 contradiction

if 
$$I_D = 0.5mA$$

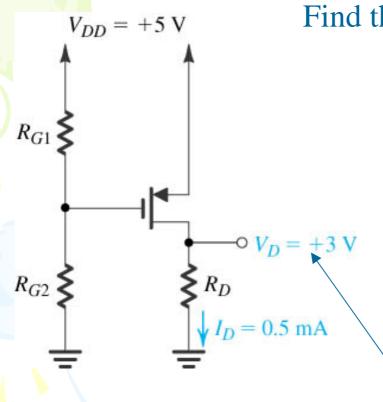
$$V_S = 6k \times 0.5m = 3V$$

$$\rightarrow V_{GS} = 2V$$

$$\rightarrow V_D = 10 - 6k \times 0.5m = 7V$$

$$\rightarrow V_D > V_G - V_t$$

## Design the circuit operate in saturation Find the range of $R_D$



$$I_D = \frac{1}{2}k_n \frac{W}{L}(V_{GS} - V_t)^2$$

$$\Rightarrow 0.5 = \frac{1}{2} \times 1 \times [V_{GS} - (-1)]^2$$

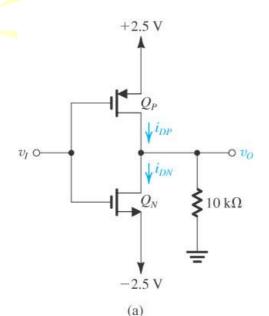
$$\Rightarrow V_{GS} = -2V$$

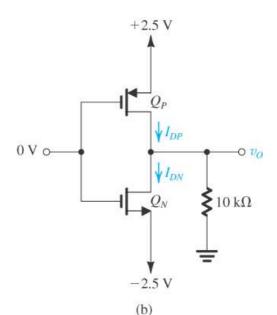
$$V_{DS} \ge V_{GS} - V_t = -2 + 1 = -1$$

$$\Rightarrow V_{D(\text{max})} = +4V$$

$$R_{D(\text{max})} = \frac{4}{0.5m} = 8k$$

$$R_{D(\text{min})} = \frac{3}{0.5m} = 6k$$





let

$$V_{nt} = -V_{pt} = 1V$$

$$K'_n(W/L)$$

$$= K'_{p}(W/L) = 1mA/V^{2}$$

#### First case : $v_I = 0V$

$$Q_p$$
 on,  $Q_n$  on

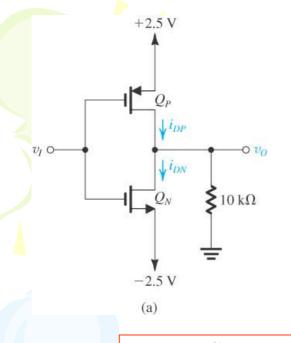
$$V_{GS(p)} = -2.5V$$

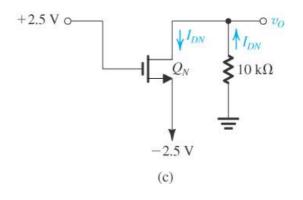
$$V_{GS(n)} = 2.5V$$

$$v_o = 0V$$

$$I_{DP} = \frac{1}{2} \times 1[-2.5 - (-1)]^2 = 1.125 mA$$

$$I_{Dn} = \frac{1}{2} \times 1[2.5 - 1]^2 = 1.125 mA$$





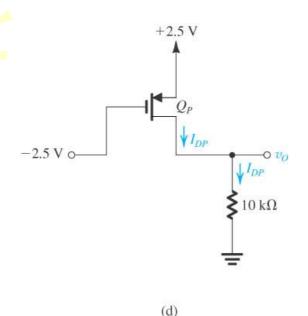
#### Second case : $v_1$ =+2.5V $Q_p$ off, $Q_n$ ohmic region

$$\frac{\mu_n C_o W}{(v_o - V_o)}$$

$$I_{D} = \frac{\mu_{n} C_{o} w}{2L} [2(v_{GS} - V_{t}) v_{DS} - v_{DS}^{2}] \approx \frac{\mu_{n} C_{o} w}{L} (v_{GS} - V_{t}) v_{DS}$$

$$V_{GS} = 5V$$
  $V_D = -2.44V = v_o$   $I_{Dn} = 1 \times 1[5-1]V_{DS}$   $V_{DS} = -2.44 + 2.5 = 0.06$   $V_{DS} = -1.44 + 2.5 = 0.06$ 

NOT gate



$$\begin{split} V_{SG} &= 5V \\ I_{Dp} &= 1 \times 1[5-1]V_{SD} \\ &= 1 \times 1[5-1](2.5 - I_{Dp} \times 10k) \\ \Rightarrow I_{Dp} &= 0.244mA \end{split}$$

### Second case: $v_I$ =-2.5V $Q_p$ ohmic region, $Q_n$ off

NOT gate

$$V_D = v_o = I_{Dv} \times 10k = 2.44V$$

$$V_{SD} = +2.5 - 2.44 = 0.06$$

$$V_{SG} - V_{t} = 5 - 1 = 4$$

$$V_{SD} \leq V_{SG} - |V_t|$$
 Ohmic region

#### Exercise 4.16 Amplifier

#### Assume

$$k_n'(W_n/L_n) = k_p'(W_p/L_p) = 1(mA/V^2)$$

$$V_{tn} = -V_{tp} = 1V$$

$$\lambda = 0$$

find

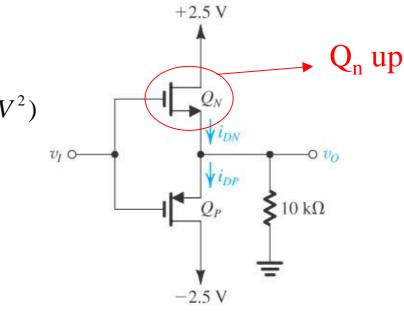
$$i_{DN}, i_{DP}, v_o$$

for

$$v_I = 0V, 2.5V, -2.5V$$

#### First case : $v_1 = 0V$

 $Q_n$  off  $Q_p$  off

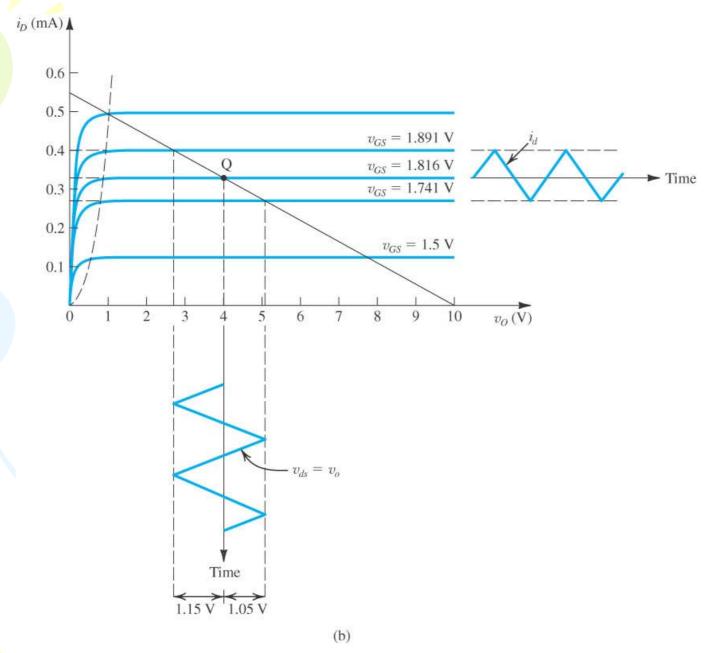


2nd case :  $v_1$ =2.5V

 $Q_n$  on  $Q_p$  off

3rd case :  $v_1$ =2.5V

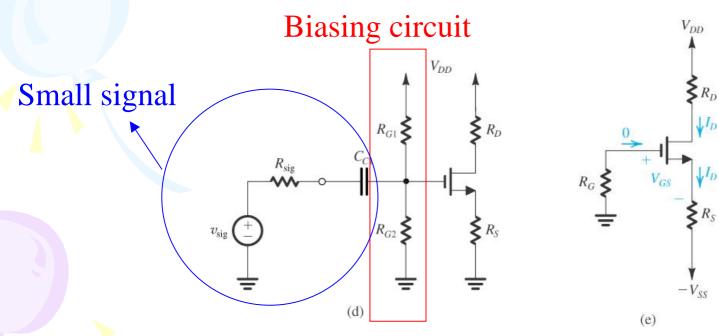
 $Q_n$  off  $Q_p$  on

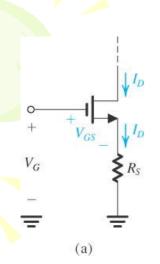


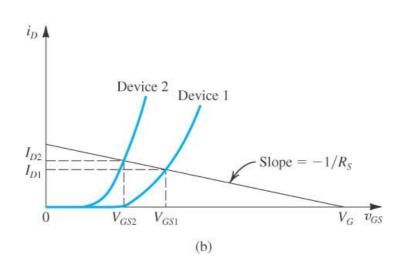
Microelectronic circuits by meiling CHEN

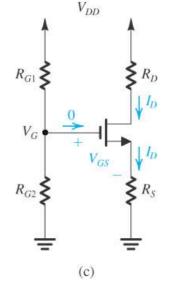
## Biasing method

- Fixed Bias by V<sub>GS</sub>
- Self Bias
- Biasing using Drain –to-Gate feedback resistor
- Biasing using constant current source





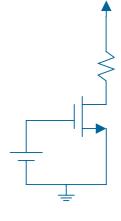




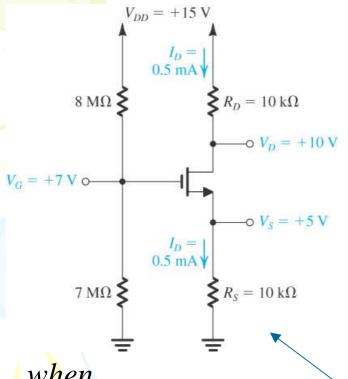
$$I_D = \frac{\mu_n C_o w}{2L} (v_{GS} - V_t)^2$$

- 1. Device change  $(V_t, C_{ox}, \frac{W}{L})$ 2. Temperature change  $(V_t, \mu_n)$

Change I<sub>D</sub>



#### Example 4.9 Fixed Bias



find

$$V_t = 1.5V$$
 Change MOSFET

$$K'_n(W/L) = 1mA/V^2$$

$$\Delta I_D = ?mA$$

$$I_D = \frac{k_n' w}{2L} (v_{GS} - V_t)^2 = \frac{1}{2} \times 1 \times (v_{GS} - 1.5)^2$$

$$v_{GS} = 7 - 10k \times I_D$$

$$\Rightarrow I_D = 0.455 mA$$

#### when

$$V_{t} = 1V$$

$$K'_n(W/L) = 1mA/V^2$$

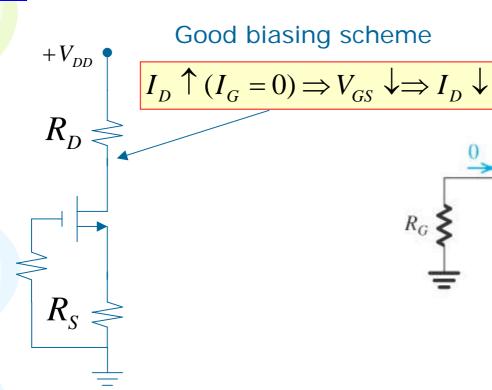
$$I_{D} = 0.5 mA$$

#### Good biasing scheme

$$I_D \uparrow \Rightarrow I_D R_S \uparrow \Rightarrow :: V_G fixed \Rightarrow V_{GS} \downarrow$$

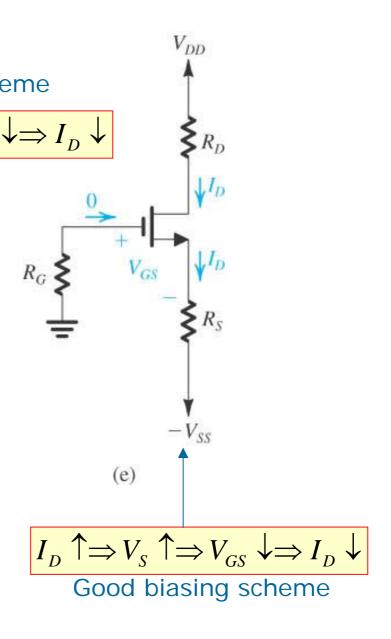
$$:: I_D = \frac{k_n'W}{2L} (v_{GS} \downarrow -V_t)^2 \Rightarrow I_D \downarrow$$

#### Self Bias

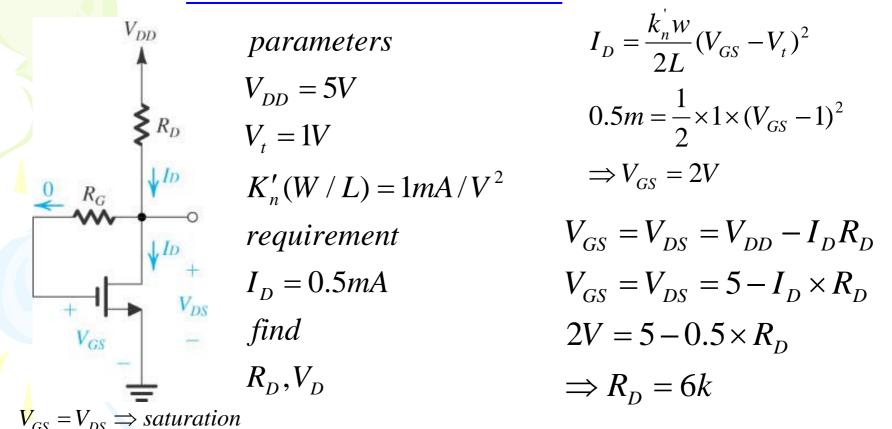


$$I_D = \frac{k_n w}{2L} (v_{GS} - V_t)^2$$

$$V_{GS} = -I_D R_S$$



#### Exercise 4.21 Drain –to-Gate feedback bias



$$I_{D} \uparrow \Rightarrow V_{D} = V_{DD} - I_{D}R_{D} \Rightarrow V_{D} \downarrow$$
$$\Rightarrow V_{GS} \Rightarrow I_{D} \downarrow$$

Good biasing scheme

